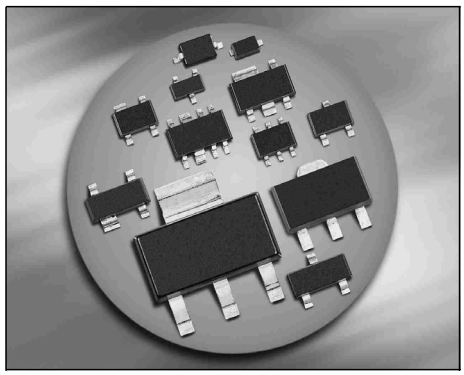
Silicon N-Channel MOSFET Tetrode



- For low noise , high gain controlled input stages up to 1GHz
- Operating voltage 5 V

ESD: **E**lectro**s**tatic **d**ischarge sensitive device, observe handling precaution!

Type	Package	Pin Configuration						Marking
BF2040	SOT143	1=S	2=D	3=G2	4=G1	-	-	NFs
BF2040R	SOT143	1=D	2=S	3=G1	4=G2	-	-	NFs
BF2040W	SOT343	1=D	2=S	3=G1	4=G2	-	-	NF

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	8	V
Continuous drain current	I_D	20	mA
Gate 1/ gate 2-source current	$\pm I_{G1/2SM}$	10	
Gate 1 (external biasing)	$+V_{G1SE}$	7	V
Total power dissipation	P_{tot}		mW
$T_S \leq 76$ °C, BF2040, BF2040R		200	
$T_S \leq 94$ °C, BF2040W		200	
Storage temperature	T_{stg}	-55 ... 150	°C
Channel temperature	T_{ch}	150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Channel - soldering point[1)]	R_{thchs}		K/W
BF2040, BF2040R		≤ 370	
BF2040W		≤ 280	

[1]For calculation of R_{thJA} please refer to Application Note Thermal Resistance

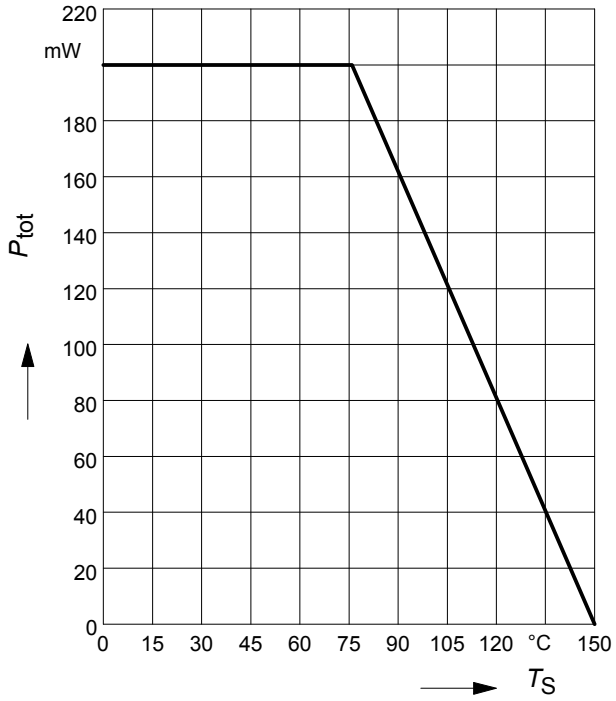
Electrical Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Drain-source breakdown voltage I_D = 20 µA, V_{G1S} = 0 , V_{G2S} = 0	$V_{(BR)DS}$	10	-	-	V
Gate1-source breakdown voltage +I_{G1S} = 10 mA, V_{G2S} = 0 , V_{DS} = 0	+$V_{(BR)G1SS}$	6	-	15	
Gate2-source breakdown voltage +I_{G2S} = 10 mA, V_{G1S} = 0 , V_{DS} = 0	+$V_{(BR)G2SS}$	6	-	15	
Gate1-source leakage current V_{G1S} = 5 V, V_{G2S} = 0 , V_{DS} = 0	+I_{G1SS}	-	-	50	nA
Gate2-source leakage current V_{G2S} = 5 V, V_{G1S} = 0 , V_{DS} = 0	+I_{G2SS}	-	-	50	
Drain current V_{DS} = 5 V, V_{G1S} = 0 , V_{G2S} = 4 V	I_{DSS}	-	-	50	µA
Drain-source current V_{DS} = 5 V, V_{G2S} = 4 V, R_{G1} = 100 kΩ	I_{DSX}	-	15	-	mA
Gate1-source pinch-off voltage V_{DS} = 5 V, V_{G2S} = 4 V, I_D = 20 µA	$V_{G1S(p)}$	0.3	0.6	-	V
Gate2-source pinch-off voltage V_{DS} = 5 V, I_D = 20 µA	$V_{G2S(p)}$	0.3	0.7	-	

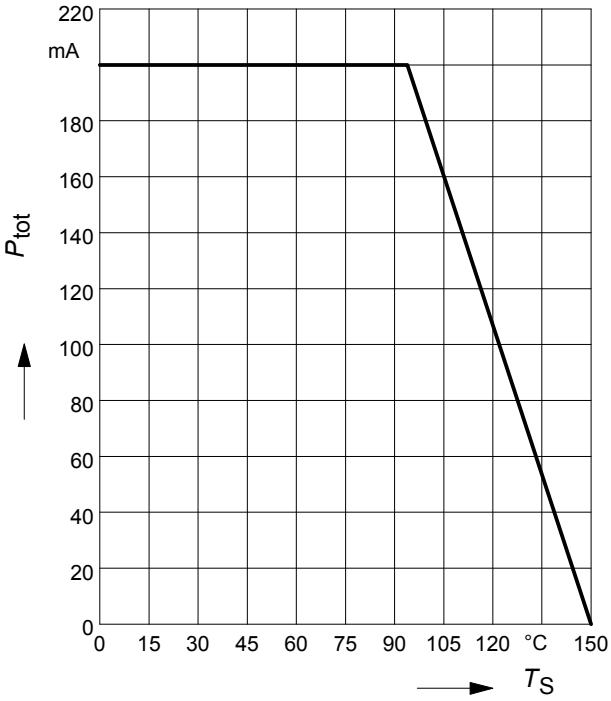
Electrical Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics - (verified by random sampling)					
Forward transconductance V_{DS} = 5 V, I_D = 15 mA, V_{G2S} = 4 V	g_{fs}	37	42	-	mS
Gate1 input capacitance V_{DS} = 5 V, I_D = 15 mA, V_{G2S} = 4 V, f = 1 MHz	C_{g1ss}	-	2.9	3.4	pF
Output capacitance V_{DS} = 5 V, I_D = 15 mA, V_{G2S} = 4 V, f = 1 MHz	C_{dss}	-	1.6	-	
Power gain V_{DS} = 5 V, I_D = 15 mA, V_{G2S} = 4 V, f = 800 MHz	G_p	20	23	-	dB
Noise figure V_{DS} = 5 V, I_D = 15 mA, V_{G2S} = 4 V, f = 800 MHz	F	-	1.6	2.2	dB
Gain control range V_{DS} = 5 V, V_{G2S} = 4 ...0 V , f = 800 GHz	ΔG_p	45	50	-	

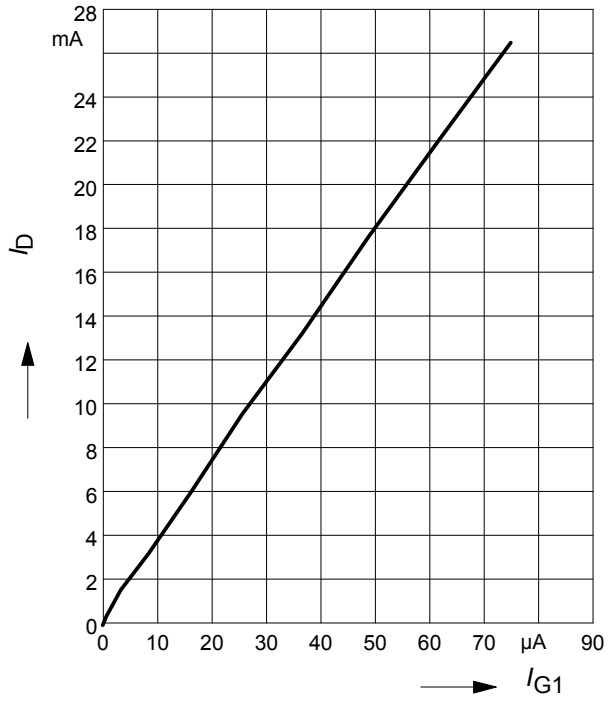
Total power dissipation $P_{tot} = f(T_S)$
BF2040, BFD2040R



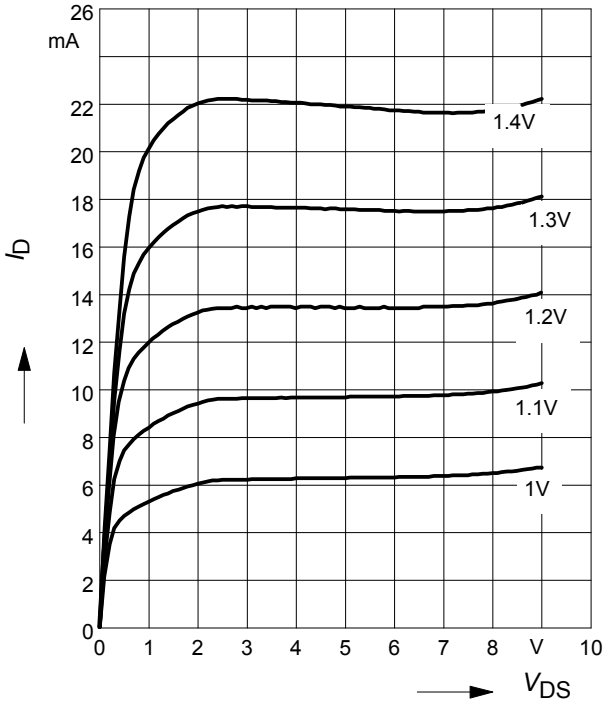
Total power dissipation $P_{tot} = f(T_S)$
BF2040W



Drain current $I_D = f(I_{G1})$
V_{G2S} = 4V



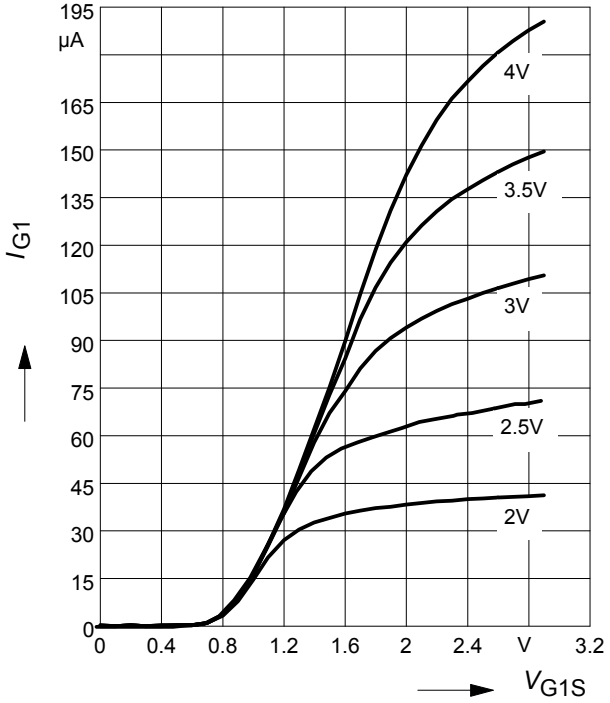
Output characteristics $I_D = f(V_{DS})$
V_{G2S} = 4 V
V_{G1S} = Parameter



Gate 1 current $I_{G1} = f(V_{G1S})$

V_{DS} = 5V

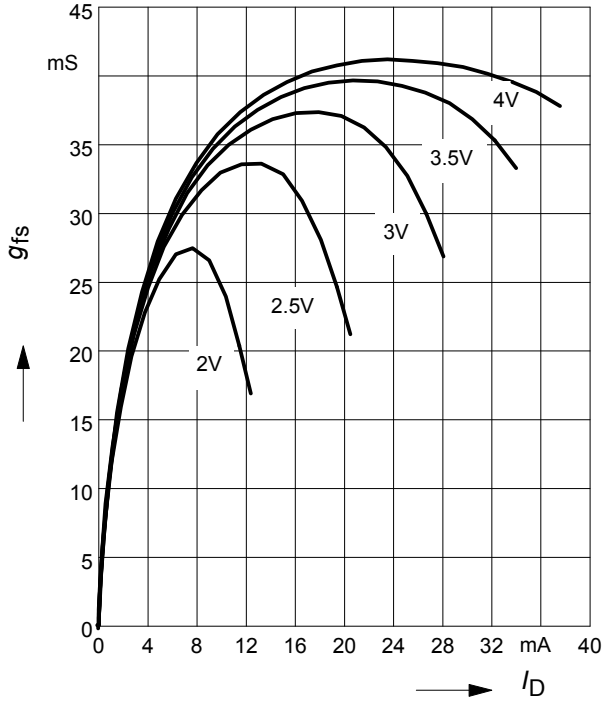
V_{G2S} = Parameter



Gate 1 forward transconductance

$g_{fs} = f(I_D)$

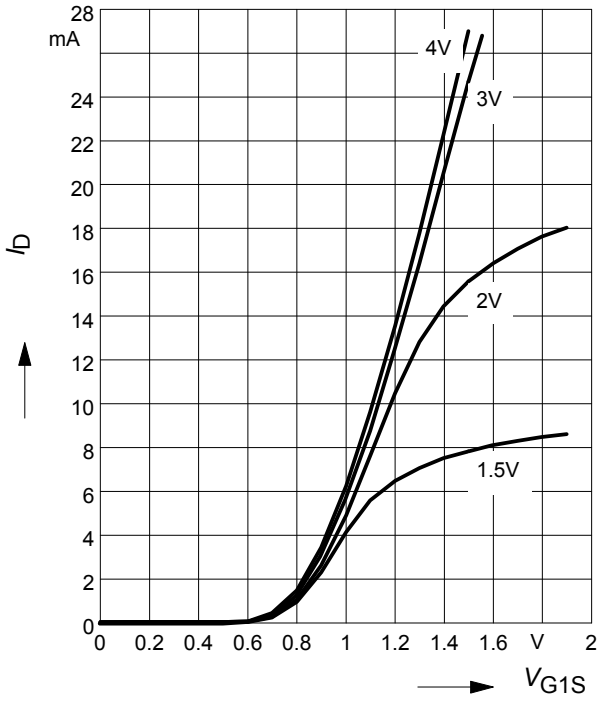
V_{DS} = 5V, V_{G2S} = Parameter



Drain current $I_D = f(V_{G1S})$

V_{DS} = 5V

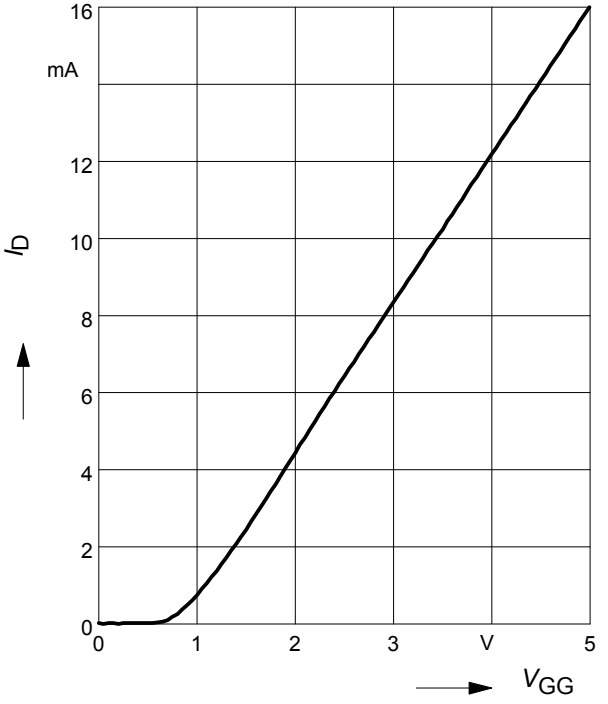
V_{G2S} = Parameter



Drain current $I_D = f(V_{GG})$

V_{DS} = 5V, V_{G2S} = 4V, R_{G1} = 80kΩ

(connected to V_{GG}, V_{GG}=gate1 supply voltage)



Drain current $I_D = f(V_{GG})$

V_{G2S} = 4V

R_{G1} = Parameter in kΩ